

## RJK6002DPD

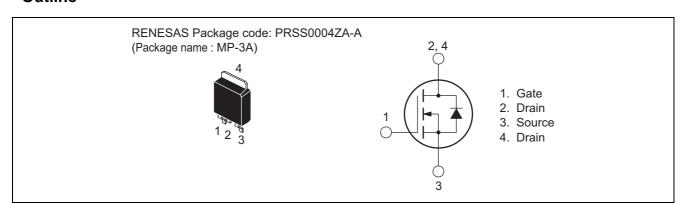
# Silicon N Channel MOS FET High Speed Power Switching

REJ03G1483-0100 Rev.1.00 Nov 09, 2006

### **Features**

- Low on-resistance
- Low leakage current
- High speed switching

### **Outline**



### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	600	V
Gate to source voltage	V <sub>GSS</sub>	±30	V
Drain current	I <sub>D</sub>	2	A
Drain peak current	I <sub>D (pulse)</sub> Note1	4	A
Body-drain diode reverse drain current	I <sub>DR</sub>	2	A
Body-drain diode reverse drain peak current	I <sub>DR (pulse)</sub> Note1	4	A
Avalanche current	I <sub>AP</sub> Note3	1	A
Avalanche energy	E <sub>AR</sub> Note3	0.05	mJ
Channel dissipation	Pch Note2	30	W
Channel to case thermal impedance	θch-c	4.17	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

2. Value at Tc = 25°C

3. STch =  $25^{\circ}$ C, Tch  $\leq 150^{\circ}$ C

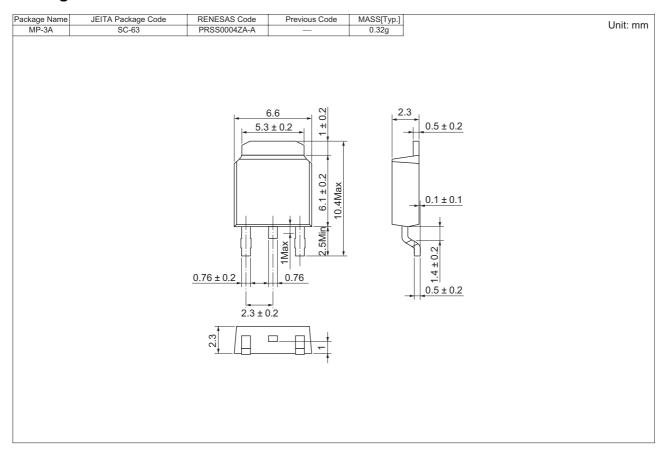
### **Electrical Characteristics**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	600	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 600 \text{ V}, V_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	V <sub>GS(off)</sub>	3.0	_	4.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R <sub>DS(on)</sub>	_	5.7	6.8	Ω	$I_D = 1 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
Input capacitance	Ciss		165		pF	V <sub>DS</sub> = 25 V
Output capacitance	Coss	_	20	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	2.5	_	pF	f = 1 MHz
Turn-on delay time	t <sub>d(on)</sub>	_	28	_	ns	I <sub>D</sub> = 1 A
Rise time	t <sub>r</sub>	_	17	_	ns	V <sub>GS</sub> = 10 V
Turn-off delay time	$t_{d(off)}$	_	47	_	ns	$R_L = 300 \Omega$
Fall time	t <sub>f</sub>	_	20	_	ns	$Rg = 10 \Omega$
Total gate charge	Qg	_	6.2	_	nC	V <sub>DD</sub> = 480 V
Gate to source charge	Qgs	_	1.1	_	nC	V <sub>GS</sub> = 10 V
Gate to drain charge	Qgd	_	3.6	_	nC	$I_D = 2 A$
Body-drain diode forward voltage	$V_{DF}$	_	0.87	1.45	V	$I_F = 2 A, V_{GS} = 0^{Note4}$
Body-drain diode reverse recovery time	t <sub>rr</sub>	_	260	_	ns	$I_F = 2 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A/}\mu\text{s}$

Notes: 4. Pulse test

### **Package Dimensions**



### **Ordering Information**

Part Name	Quantity	Shipping Container
RJK6002DPD-00-J2	3000 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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